L Number	Hits	Search Text	DB	Time stamp
- Number	9844	((diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 10:15
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$4)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10015	((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:54
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$45)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/01 03 53
-	7329	((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:57
		deformable elastom\$5 resilient\$5) near2	US-PGPUB; EPO; JPO;	
		(conduct\$45)).clm.		
			DERWENT; IBM TDB	
_	10011	((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:57
-	10011	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	2002/10/01 07:37
		(conduct\$5)).clm.	EPO; JPO;	
		(6011446643)).6114.	DERWENT;	
			IBM TDB	
_	733	(((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:57
	,33	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.	EPO; JPO;	
		(00.000),,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	DERWENT;	
			IBM TDB	
_	264	((((diaphragm membrane elastic\$5 flexible	USPĀT;	2002/10/01 07:57
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.	DERWENT;	
			IBM TDB	
_	53		USPĀT;	2003/06/26 18:36
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.) and (concentration	DERWENT;	
		impurity purity)	IBM_TDB	1
-	17		USPAT;	2003/06/26 18:28
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.) and (concentration	DERWENT;	
		impurity purity).clm.	IBM_TDB	
_	700	(216/2).CCLS.	USPAT;	2003/06/26 18:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	92	((216/2).CCLS.) and impurit\$4	IBM_TDB USPAT;	2003/06/26 18:37
_	32	((210/2).CCLS.) and impulity4	US-PGPUB;	2003/00/20 10.37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	(((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:39
	1	concentration) and etch near1 pit	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	((((216/2).CCLS.) and impurit\$4 near3	USPĀT;	2003/06/26 18:39
		concentration) and etch near1 pit) and	US-PGPUB;	
		diaphragm	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
_	23		USPAT;	2003/06/26 18:41
	1	concentration	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/06/06 10 15
_	20	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2003/06/26 18:48
		concentration) and etch	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
L	<u> </u>	I	IBM TDB	<u> </u>

-	15	((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:32
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)	EPO; JPO; DERWENT;	
		elastomas resilientas)	IBM TDB	
1_	3	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:26
		concentration and etch and (diaphragm	US-PGPUB;	2003/00/20 19.20
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and etch near3	DERWENT;	
		(pit hole groove dip)	IBM TDB	
_	3	(((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:49
		concentration) and etch near3 (pit hole	US-PGPUB;	
		groove dip)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:57
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and electrode near3 dielectric near3 (film layer support	DERWENT; IBM TDB	
		substrate cover\$4)	I TOW _ I DO	
_	1	((((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:55
		concentration and etch and (diaphragm	US-PGPUB;	
	1	membrane elastic\$5 flexible deformable	EPO; JPO;	
1		elastom\$5 resilient\$5)) and electrode	DERWENT;	
		near3 dielectric near3 (film layer support	IBM_TDB	
		substrate cover\$4)) and pressure		
-	1	(((((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:55
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and electrode	DERWENT;	
		near3 dielectric near3 (film layer support substrate cover\$4)) and pressure) and	IBM_TDB	
		silicon		
_	11	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:04
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and pressure	DERWENT;	
		·	IBM_TDB	
_	6	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:27
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and pressure near3 (sens\$4 measur\$3 detect test transducer	DERWENT;	
		qauge monitor evaluate estimat\$4 identif\$4	IBM_TDB	
		indicat\$4)		
_	44167	impurit\$4 near3 concentration	USPAT;	2003/06/26 19:27
			US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1092	(impurit\$4 near3 concentration) and	USPAT;	2003/06/26 19:29
		pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	
		test transducer gauge monitor evaluate	EPO; JPO;	
		estimat\$4 identif\$4 indicat\$4)	DERWENT; IBM TDB	
_	18	((impurit\$4 near3 concentration) and	USPAT;	2003/06/26 19:30
		pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	2555,00,20 15.50
		test transducer gauge monitor evaluate	EPO; JPO;	
		estimat\$4 identif\$4 indicat\$4)) and etch	DERWENT;	
1		near3 (pit groove hole dip)	IBM TDB	
-	13	(((impurit\$4 near3 concentration) and	USPĀT;	2003/06/26 19:32
		pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	
		test transducer gauge monitor evaluate	EPO; JPO;	
		estimat\$4 identif\$4 indicat\$4)) and etch	DERWENT;	
		near3 (pit groove hole dip)) and	IBM_TDB	
	1	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)		
1	l	Gerormanie erascomás resirrentás)	<u> </u>	l

Page 2

						٠.
-	29	(diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 1	10:51	
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;			
		conduct\$4 same etch\$4 same density	EPO; JPO;			
			DERWENT;			
		/discharge manhuana alaghiach flauible	IBM_TDB USPAT;	2004/04/15 1	0.22	
-	3	(diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2	USPAT; US-PGPUB;	2004/04/15 1	10:23	
			EPO; JPO;			
		conduct\$4 same etch\$4 same pit same	DERWENT;			
1		density	IBM TDB			1
_	658	(361/283.1-283.4).CCLS.	USPAT;	2004/04/15 1	0.24	
-	030	(301/203.1-203.4).0013.	US-PGPUB;	2004/04/13 1	.0.24	1
			EPO; JPO;			
			DERWENT;			
			IBM TDB			
_	1	((361/283.1-283.4).CCLS.) and etch\$4 same	USPĀT;	2004/04/15 1	10:35	
	*	pit same density	US-PGPUB;			
			EPO; JPO;			l
			DERWENT;			l
			IBM TDB			ı
_	0	((361/283.1-283.4).CCLS.) and etch\$4 near3	USPAT;	2004/04/15 1	10:36	
1		(pit\$4 hole\$4 groove\$4 recess\$4 opening\$\$)	US-PGPUB;			
1		same density	EPO; JPO;			1.
1			DERWENT;			l
			IBM TDB			
_	0	((361/283.1-283.4).CCLS.) and etch\$4 near3	USPAT;	2004/04/15 1	10:38	
1	1	(pit\$4 hole\$4 groove\$4 recess\$4 opening\$4)	US-PGPUB;			
		same density	EPO; JPO;	ĺ		
		-	DERWENT;			1
			IBM_TDB			
-	919	((361/283.1-283.4).CCLS.) and 73/754.ccls.	USPAT;	2004/04/15 1	10:48	
		or 73/718.ccls. or 73/724.ccls.	US-PGPUB;			
			EPO; JPO;			
			DERWENT;			1
			IBM_TDB	<u>-</u>		
-	2		USPAT;	2004/04/15	10:48	
		73/754.ccls. or 73/718.ccls. or	US-PGPUB;			ı
		73/724.ccls.) and etch\$4 near3 (pit\$4	EPO; JPO;			ı
		opening\$4 groove\$4 recess\$4 hole\$4) same	DERWENT;			ı
		density	IBM_TDB USPAT;	2004/04/15	10.47	
-	2	(((361/283.1-283.4).CCLS.) and	US-PGPUB;	2004/04/13	10.47	
•		73/754.ccls. or 73/718.ccls. or	EPO; JPO;			
		73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4	DERWENT;			
		qroove\$4 recess\$4 hole\$4) same density	IBM TDB			1.
1_	2	(((361/283.1-283.4).CCLS.) and	USPAT;	2004/04/15	10:48	1
-	-	73/754.ccls. or 73/718.ccls. or	US-PGPUB;	-331, 31, 13		
		73/724.ccls.) and (etch\$4 concentration	EPO; JPO;			ļ
		impurit\$4 dop\$4) near3 (pit\$4 opening\$4	DERWENT;			1
		groove\$4 recess\$4 hole\$4) same density	IBM TDB			1
_	0		USPĀT;	2004/04/15	10:47	
		73/754.ccls. or 73/718.ccls. or	US-PGPUB;			
		73/724.ccls.) and (etch\$4 concentration	EPO; JPO;			
		impurit\$4 dop\$4) near3 (pit\$4 opening\$4	DERWENT;			
		groove\$4 recess\$4 hole\$4) near4 density	IBM_TDB			
-	1694	1 7	USPĀT;	2004/04/15	10:48	
		or 73/718.ccls. or 73/724.ccls.	US-PGPUB;	1		
			EPO; JPO;	-		
			DERWENT;			
			IBM_TDB			
-	4	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2004/04/15	10:48	
		or 73/718.ccls. or 73/724.ccls.) and	US-PGPUB;			
		etch\$4 near3 (pit\$4 opening\$4 groove\$4	EPO; JPO;			1
		recess\$4 hole\$4) same density	DERWENT;			
		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	IBM_TDB	0004/04/15	10.40	
-	4	(((361/283.1-283.4).CCLS.) or 73/754.ccls.	USPAT;	2004/04/15	10:49	1
		or 73/718.ccls. or 73/724.ccls.) and	US-PGPUB;			1
		(etch\$4 concentration impurit\$4 dop\$4)	EPO; JPO;			
	1	near3 (pit\$4 opening\$4 groove\$4 recess\$4	DERWENT;			
i	1	hole\$4) same density	IBM TDB	1		-

-	261	1 (USPAT;	2004/04/15 10:52	2
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;		
		conduct\$4 same etch\$4 same (pit\$4 hole\$4	EPO; JPO;		
		groove\$4 recess\$4 opening\$4)	DERWENT;		
	_		IBM_TDB	0004/04/15 10 5/	۱ ـ
-	8	(((361/283.1-283.4).CCLS.) and	USPAT;	2004/04/15 10:52	۱ ک
		73/754.ccls. or 73/718.ccls. or	US-PGPUB;		
		73/724.ccls.) and ((diaphragm membrane	EPO; JPO;		
		elastic\$5 flexible deformable elastom\$5	DERWENT;		
1		resilient\$5) near2 conduct\$4 same etch\$4	IBM_TDB		
		same (pit\$4 hole\$4 groove\$4 recess\$4			
	1.2	opening\$4)) (diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 10:53	٦
_	12	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	2004/04/13 10.3	1
		conduct\$4 same etch\$4 same (pit\$4 hole\$4	EPO; JPO;		- [
		groove\$4 recess\$4 opening\$4) same density	DERWENT;		- 1
		drooved recessed obsuringed, same density	IBM TDB		- 1